

MOSFETs Silicon N-channel MOS (U-MOSIX-H)

TK5R3A06PL

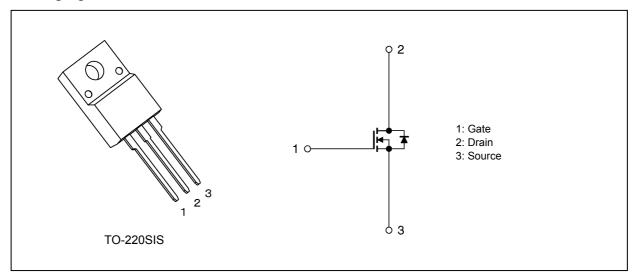
1. Applications

- High-Efficiency DC-DC Converters
- · Switching Voltage Regulators
- · Motor Drivers

2. Features

- (1) High-speed switching
- (2) Small gate charge: $Q_{SW} = 11 \text{ nC (typ.)}$
- (3) Small output charge: $Q_{oss} = 32 \text{ nC (typ.)}$
- (4) Low drain-source on-resistance: $R_{DS(ON)} = 4.1 \text{ m}\Omega$ (typ.) ($V_{GS} = 10 \text{ V}$)
- (5) Low leakage current: $I_{DSS} = 10 \mu A \text{ (max) (V}_{DS} = 60 \text{ V)}$
- (6) Enhancement mode: V_{th} = 1.5 to 2.5 V (V_{DS} = 10 V, I_D = 0.3 mA)

3. Packaging and Internal Circuit



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4. Absolute Maximum Ratings (Note) (Ta = 25 °C unless otherwise specified)

Characteristics				Rating	Unit
Drain-source voltage			V_{DSS}	60	V
Gate-source voltage			V_{GSS}	±20	
Drain current (DC)	(T _c = 25 °C)	(Note 1)	I _D	56	Α
Drain current (DC)	(Silicon limit)	(Note 1), (Note 2)	I_D	62	Α
Drain current (pulsed)	(t = 100 μs)	(Note 1)	I_{DP}	280	Α
Power dissipation	(T _c = 25 °C)		P_{D}	36	W
Single-pulse avalanche energy		(Note 3)	E _{AS}	29	mJ
Single-pulse avalanche current		(Note 3)	I _{AS}	56	Α
Channel temperature			T_ch	175	°C
Storage temperature			T_{stg}	-55 to 175	°C
Isolation voltage (RMS)	(t = 1.0 s)		V _{ISO(RMS)}	2000	V
Mounting torque			TOR	0.6	N · m

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

5. Thermal Characteristics

Characteristics			Max	Unit
Channel-to-case thermal resistance	(T _c = 25 °C)	R _{th(ch-c)}	4.16	°C/W
Channel-to-ambient thermal resistance	(T _a = 25 °C)	R _{th(ch-a)}	62.5	

Note 1: Ensure that the channel temperature does not exceed 175 °C.

Note 2: Limited by silicon chip capability.

Note 3: V_{DD} = 48 V, T_{ch} = 25 °C (initial), L = 7.3 μ H, I_{AS} = 56 A

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.



6. Electrical Characteristics

6.1. Static Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I _{GSS}	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±0.1	μА
Drain cut-off current	I _{DSS}	V _{DS} = 60 V, V _{GS} = 0 V	_	_	10	
Drain-source breakdown voltage	V _{(BR)DSS}	I _D = 10 mA, V _{GS} = 0 V	60	_	_	٧
Drain-source breakdown voltage (Note 4)	V _{(BR)DSX}	I _D = 10 mA, V _{GS} = -20 V	45	_	_	
Gate threshold voltage	V_{th}	$V_{DS} = 10 \text{ V}, I_D = 0.3 \text{ mA}$	1.5	_	2.5	
Drain-source on-resistance	R _{DS(ON)}	V _{GS} = 4.5 V, I _D = 14 A	_	6.2	9.3	mΩ
		V _{GS} = 10 V, I _D = 28 A	_	4.1	5.3	

Note 4: If a reverse bias is applied between gate and source, this device enters $V_{(BR)DSX}$ mode. Note that the drain-source breakdown voltage is lowered in this mode.

6.2. Dynamic Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C _{iss}	V _{DS} = 30 V, V _{GS} = 0 V, f = 1 MHz	_	2380	_	pF
Reverse transfer capacitance	C _{rss}		_	50	_	
Output capacitance	C _{oss}		_	470	_	
Gate resistance	r _g	_	_	1.4	_	Ω
Switching time (rise time)	t _r	See Fig. 6.2.1	_	6	_	ns
Switching time (turn-on time)	t _{on}		_	19	_	
Switching time (fall time)	t _f		_	7	_	
Switching time (turn-off time)	t _{off}		_	35	_	

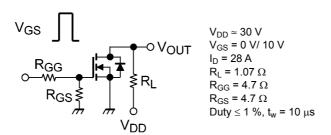


Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus	Q_g	$V_{DD} \approx 30 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 28 \text{ A}$	_	36		nC
gate-drain)		$V_{DD} \approx 30 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 28 \text{ A}$	_	18		
Gate-source charge 1	Q _{gs1}	$V_{DD} \approx 30 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 28 \text{ A}$	_	9.0		
Gate-drain charge	Q_{gd}		_	6.5	_	
Gate switch charge	Q_{SW}		_	11	_	
Output charge	Q_{oss}	V _{DS} = 30 V, V _{GS} = 0 V, f = 1 MHz	_	32	_	



6.4. Source-Drain Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Reverse drain current (pulsed) (Note 5)	I _{DRP} (t = 100 μs)	_	ı	ı	280	Α
Diode forward voltage	V_{DSF}	I _{DR} = 56 A, V _{GS} = 0 V			-1.5	V
Reverse recovery time	t _{rr}	I _{DR} = 14 A, V _{GS} = 0 V,	_	40	_	ns
Reverse recovery charge	Q _{rr}	-dI _{DR} /dt = 100 A/μs	_	38		nC

Note 5: Ensure that the channel temperature does not exceed 175 °C.

7. Marking (Note)

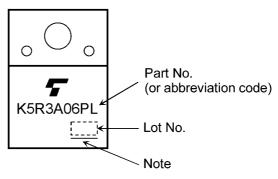


Fig. 7.1 Marking

Note: A line under a Lot No. identifies the indication of product Labels.

Not underlined: [[Pb]]/INCLUDES > MCV

Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product.

The RoHS is the Directive 2011/65/EU of the European Parliament and of the Council of 8 June 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.



8. Characteristics Curves (Note)

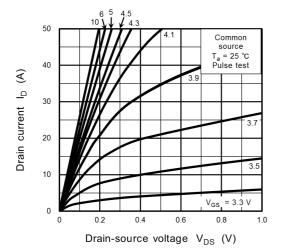


Fig. 8.1 I_D - V_{DS}

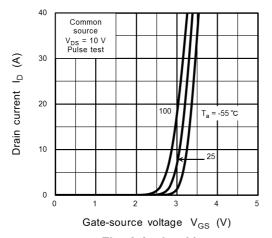


Fig. 8.3 I_D - V_{GS}

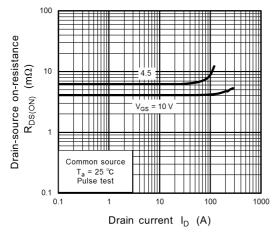


Fig. 8.5 R_{DS(ON)} - I_D

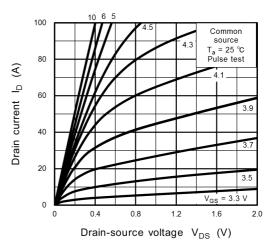


Fig. 8.2 I_D - V_{DS}

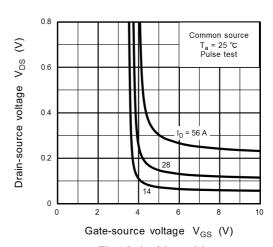


Fig. 8.4 VDS - VGS

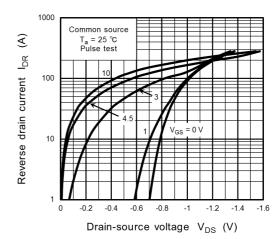


Fig. 8.6 IDR - VDS



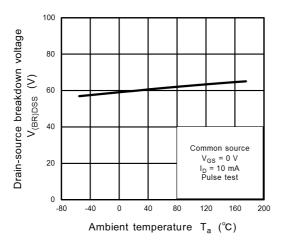


Fig. 8.7 V_{(BR)DSS} - T_a

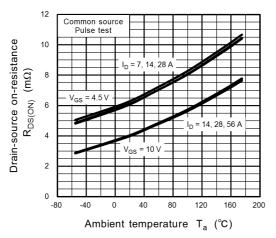


Fig. 8.9 R_{DS(ON)} - T_a

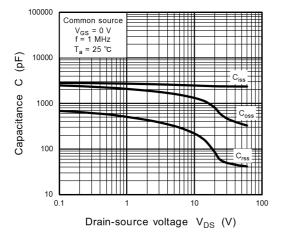


Fig. 8.11 Capacitance - V_{DS}

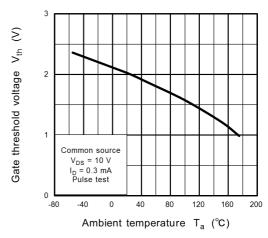


Fig. 8.8 V_{th} - T_a

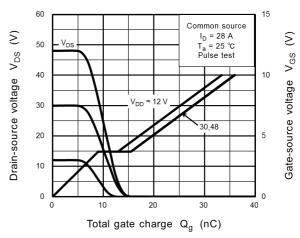


Fig. 8.10 Dynamic Input/Output Characteristics

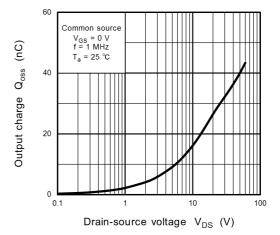


Fig. 8.12 Q_{oss} - V_{DS}



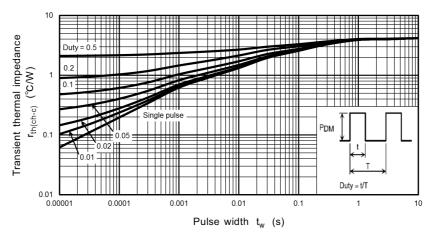
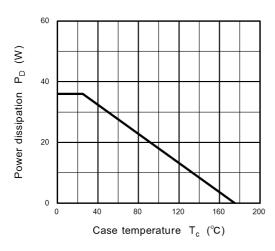


Fig. 8.13 r_{th} - t_w (Guaranteed Maximum)



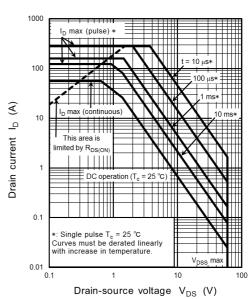


Fig. 8.14 P_D - T_c (Guaranteed Maximum)

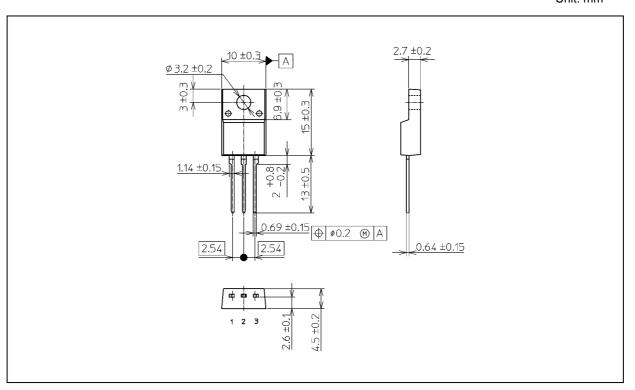
Fig. 8.15 Safe Operating Area (Guaranteed Maximum)

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



Package Dimensions

Unit: mm



Weight: 1.56 g (typ.)

Package Name(s)	
TOSHIBA: 2-10U1S	
Nickname: TO-220SIS	



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